L	Hits	Search Text	DB	Time stamp
Number			*****	2002/06/00
1	260	electroplating adj3 mask	USPAT;	2003/06/20
			EPO; JPO; DERWENT	14:22
2	0	(electroplating adj3 mask) and PECVD	USPAT;	2003/06/20
2		(electropiating adjo mask) and PECVD	EPO; JPO;	14:24
			DERWENT	19.23
3	188	438/674.ccls.	USPAT;	2003/06/20
] 3	100	1307071.0015.	EPO; JPO;	14:24
			DERWENT	-110
4	1	(electroplating adj3 mask) and	USPAT;	2003/06/20
		438/674.ccls.	EPO; JPO;	14:25
			DERWENT	
5	50475	electroplat\$3	USPAT;	2003/06/20
			EPO; JPO;	14:26
			DERWENT	
6	37	electroplat\$3 and 438/674.ccls.	USPAT;	2003/06/20
			EPO; JPO;	14:27
_	1-	/-lastnenlat02 and 420/6741- \	DERWENT	2003/06/20
7	15	(electroplat\$3 and 438/674.ccls.) and trench	USPAT; EPO; JPO;	14:34
		CLENCII	DERWENT	14.34
8	106	438/674.ccls. and mask\$3	USPAT;	2003/06/20
"	100	1307 071.0013. una maskys	EPO; JPO;	14:41
			DERWENT	
9	22	(438/674.ccls. and mask\$3) and	USPAT;	2003/06/20
		electroplat\$3	EPO; JPO;	14:45
			DERWENT	
10	52633	trench	USPAT;	2003/06/20
			EPO; JPO;	14:46
	004000		DERWENT	2002/06/20
11	824802	copper tantalum titanium tungsten	USPAT;	2003/06/20 14:46
			EPO; JPO; DERWENT	14:46
12	9812	(copper tantalum titanium tungsten) and	USPAT;	2003/06/20
12] 3012	trench	EPO; JPO;	14:46
			DERWENT	
13	588262	"aluminum nitride" "Silicon Nitride"	USPAT;	2003/06/20
		"tantalum nitride" "titanium nitride" aln	EPO; JPO;	14:48
		SiN Tan Tin "Aluminium oxide" "Silicon	DERWENT	
		oxide" "TAntalum oxide" "Titanium oxide"		
L		Al203 SiO2 TaO TiO		
14	7282	("aluminum nitride" "Silicon Nitride"	USPAT;	2003/06/20
		"tantalum nitride" "titanium nitride" aln	EPO; JPO;	14:48
		SiN Tan Tin "Aluminium oxide" "Silicon oxide" "TAntalum oxide" "Titanium oxide"	DERWENT	
		Al203 SiO2 TaO TiO) and ((copper tantalum		
	1	titanium tungsten) and trench)		
15	806	(("aluminum nitride" "Silicon Nitride"	USPAT;	2003/06/20
		"tantalum nitride" "titanium nitride" aln	EPO; JPO;	14:48
		SiN Tan Tin "Aluminium oxide" "Silicon	DERWENT	
		oxide" "TAntalum oxide" "Titanium oxide"		
		Al203 SiO2 TaO TiO) and ((copper tantalum		1
	1	titanium tungsten) and trench)) and		
1.6	7.00	electroplat\$3	HCDATE:	2002/06/20
16	/60	((("aluminum nitride" "Silicon Nitride"	USPAT;	2003/06/20
	1	"tantalum nitride" "titanium nitride" aln SiN Tan Tin "Aluminium oxide" "Silicon	EPO; JPO; DERWENT	17:47
1		oxide" "TAntalum oxide" "Titanium oxide"	DEKARINI	1
	1	Al203 SiO2 TaO TiO) and ((copper tantalum		
İ		titanium tungsten) and trench)) and		
		electroplat\$3) and (partial portion		
	l	exposed)		

17	1 205	(((("aluminum nitride" "Silicon Nitride"	USPAT;	2003/06/20
. 17	203	"tantalum nitride" "titanium nitride" aln SiN Tan Tin "Aluminium oxide" "Silicon oxide" "TAntalum oxide" "Titanium oxide" Al203 Si02 TaO TiO) and ((copper tantalum titanium tungsten) and trench)) and electroplat\$3) and (partial portion exposed)) and PECVD	EPO; JPO; DERWENT	14:49
18	1727061	((((("aluminum nitride" "Silicon Nitride" "tantalum nitride" "titanium nitride" aln SiN Tan Tin "Aluminium oxide" "Silicon oxide" "TAntalum oxide" "Titanium oxide" Al203 Si02 TaO TiO) and ((copper tantalum titanium tungsten) and trench)) and electroplat\$3) and (partial portion exposed)) and PECVD) and copper cu Platinum Pt Palladium Pd Nickel Ni	USPAT; EPO; JPO; DERWENT	2003/06/20 14:50
19	203	((((("aluminum nitride" "Silicon Nitride" "tantalum nitride" "titanium nitride" aln SiN Tan Tin "Aluminium oxide" "Silicon oxide" "TAntalum oxide" "Titanium oxide" Al203 Si02 Ta0 Ti0) and ((copper tantalum titanium tungsten) and trench)) and electroplat\$3) and (partial portion exposed)) and PECVD) and copper cu Platinum Pt Palladium Pd Nickel Ni) and (((("aluminum nitride" "Silicon Nitride" "tantalum nitride" "titanium nitride" aln SiN Tan Tin "Aluminium oxide" "Silicon oxide" "TAntalum oxide" "Titanium oxide" Al203 Si02 Ta0 Ti0) and ((copper tantalum titanium tungsten) and trench)) and electroplat\$3) and (partial	USPAT; EPO; JPO; DERWENT	2003/06/20 14:50
20	142828	portion exposed)) and PECVD) ((((((("aluminum nitride" "Silicon Nitride" "tantalum nitride" "titanium nitride" aln SiN Tan Tin "Aluminium oxide" "Silicon oxide" "TAntalum oxide" "Titanium oxide" Al203 Si02 Ta0 Ti0) and ((copper tantalum titanium tungsten) and trench)) and electroplat\$3) and (partial portion exposed)) and PECVD) and copper cu Platinum Pt Palladium Pd Nickel Ni) and (((("aluminum nitride" "Silicon Nitride" "tantalum nitride" "titanium nitride" aln SiN Tan Tin "Aluminium oxide" "Silicon oxide" "TAntalum oxide" "Titanium oxide" Al203 Si02 Ta0 Ti0) and ((copper tantalum titanium tungsten) and trench)) and electroplat\$3) and (partial portion exposed)) and PECVD)) and "side wall" sidewall	USPAT; EPO; JPO; DERWENT	2003/06/20 14:51

ſ	21	76		USPAT;	2003/06/20
-			Nitride" "tantalum nitride" "titanium	EPO; JPO;	15:15
ı			nitride" aln SiN Tan Tin "Aluminium	DERWENT	
1			oxide" "Silicon oxide" "TAntalum oxide"		
l			"Titanium oxide" Al2O3 SiO2 TaO TiO) and		
			((copper tantalum titanium tungsten) and		
I			trench)) and electroplat\$3) and (partial		
1			portion exposed)) and PECVD) and copper		
١			cu Platinum Pt Palladium Pd Nickel Ni)		
I			and ((((("aluminum nitride" "Silicon		
١			Nitride" "tantalum nitride" "titanium		
			nitride" aln SiN Tan Tin "Aluminium		
١			oxide" "Silicon oxide" "TAntalum oxide"		
1			"Titanium oxide" Al2O3 SiO2 TaO TiO) and		
			((copper tantalum titanium tungsten) and		
١			trench)) and electroplat\$3) and (partial		
1			portion exposed)) and PECVD)) and "side		
١			wall" sidewall) and (((((("aluminum		
			nitride" "Silicon Nitride" "tantalum		
			nitride" "titanium nitride" aln SiN Tan		
			Tin "Aluminium oxide" "Silicon oxide"		
			"TAntalum oxide" "Titanium oxide" Al2O3		
			SiO2 TaO TiO) and ((copper tantalum		
1			titanium tungsten) and trench)) and		
1			electroplat\$3) and (partial portion		
1			exposed)) and PECVD) and copper cu		
			Platinum Pt Palladium Pd Nickel Ni) and		
			((((("aluminum nitride" "Silicon Nitride"		
ĺ			"tantalum nitride" "titanium nitride" aln		
1			SiN Tan Tin "Aluminium oxide" "Silicon		
			oxide" "TAntalum oxide" "Titanium oxide"		
			Al203 SiO2 TaO TiO) and ((copper tantalum		
			titanium tungsten) and trench)) and		
-			electroplat\$3) and (partial portion		
1	22	71881	exposed)) and PECVD))	USPAT;	2003/06/20
1	44	/1001	electroless electroplat\$3	EPO; JPO;	15:15
-				DERWENT	13.13
	23	260	(electroless electroplat\$3) and	USPAT;	2003/06/20
	د ع	200	(electroplating adj3 mask)	EPO; JPO;	15:29
			(erectobiating adjo mask)	DERWENT	10.29
	24	3	"6432820"	USPAT;	2003/06/20
	67	3	0332020	EPO; JPO;	15:29
				DERWENT	10.27
- 1		,			l